

## **isc Silicon NPN Power Transistor**

## 2SC3850

### DESCRIPTION

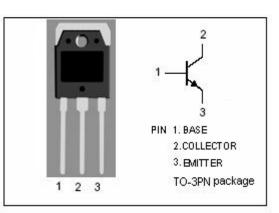
- High Collector-Emitter Sustaining Voltage-: V<sub>CEO(SUS)</sub>= 400V(Min)
- · Good Linearity of hFE
- High Collector Current
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

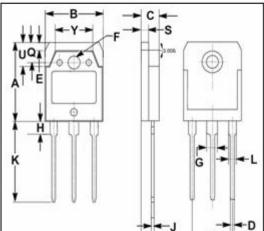
### APPLICATIONS

• Designed for power switching and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)					
SYMBOL	PARAMETER	VALUE	UNIT		
V <sub>CBO</sub>	Collector-Base Voltage	500	V		
Vces	Collector-Emitter Voltage	500	V		
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V		
V <sub>EBO</sub>	Emitter-Base voltage	7	V		
lc	Collector Current-Continuous	20	A		
I <sub>CM</sub>	Collector Current-Peak	30	A		
Ів	Base Current-Continuous	6	А		
Pc	Collector Power Dissipation @ $T_c$ =25°C	125	W		
	Collector Power Dissipation @ $T_a=25^{\circ}C$	2.5			
TJ	Junction Temperature	150	°C		
T <sub>stg</sub> Storage Temperature Range		-55~150	°C		

### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)





	mm		
DIM	MIN	MAX	
Α	19.60	20.10	
В	15.50	15.70	
С	4.70	4.90	
D	0.90	1.10	
E	1.90	2.10	
F	3.40	3.60	
G	2.90	3.20	
Н	3.20	3.40	
J	0.595	0.605	
Κ	20.00	20.70	
L	1.90	2.20	
N	10.89	10.91	
Q	4.90	5.10	
R	3.35	3.45	
S	1.995	2.100	
U	5.90	6.10	
Y	9.90	10.10	

isc website: www.iscsemi.com



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### **ELECTRICAL CHARACTERISTICS**

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> =0	400			V
$V_{\text{CE}(\text{sat})}$	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 2A			1.0	V
$V_{\text{BE}(\text{sat})}$	Base-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 2A			1.5	V
I <sub>СВО</sub>	Collector Cutoff Current	V <sub>CB</sub> = 500V ; I <sub>E</sub> = 0			100	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			100	μA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 2A ; V <sub>CE</sub> = 5V	15			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 10A ; V <sub>CE</sub> = 5V	10			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 10V; f= 1MHz		15		MHz

Switching Times

t <sub>on</sub>	Turn-on Time			1.0	μ <b>S</b>
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 10A, I <sub>B1</sub> = -I <sub>B2</sub> = 2A; V <sub>CC</sub> = 125V		2.5	μ <b>s</b>
t <sub>f</sub>	Fall Time			1.0	μ S

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